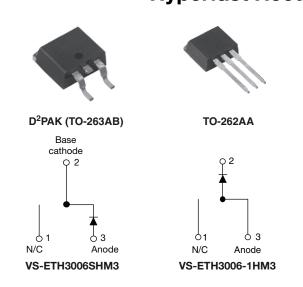
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VS-ETH3006SHM3, VS-ETH3006-1HM3

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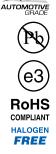
Hyperfast Rectifier, 30 A FRED Pt[®]



PRIMARY CHARACTERISTICS								
I _{F(AV)}	30 A							
V _R	600 V							
V _F at I _F	1.4 V							
t _{rr} (typ.)	27 ns							
T _J max.	175 °C							
Package	D ² PAK (TO-263AB), TO-262AA							
Circuit configuration	Single							

FEATURES

- · Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- AEC-Q101 gualified, meets JESD 201 class 1A whisker test



- Meets MSL level 1, J-STD-020, per LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC Boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS					
Repetitive peak reverse voltage	V _{RRM}		600	V					
Average rectified forward current	I _{F(AV)}	T _C = 95 °C	30	٨					
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	180	A					
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS					
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-					
Forward voltage	V _F	I _F = 30 A	-	2.0	2.65	V				
		I _F = 30 A, T _J = 150 °C	-	1.4	1.8					
Deverse leekeese eurrent	I _R	$V_{R} = V_{R}$ rated	-	0.02	30					
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	50	300	μΑ				
Junction capacitance	CT	V _R = 600 V	-	20	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

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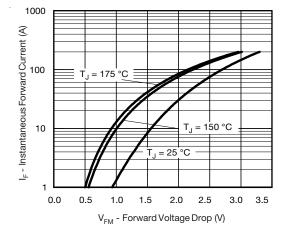
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DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS				
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50$	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		26	35				
Reverse recovery time	t _{rr}	T _J = 25 °C		-	26	-	ns			
		T _J = 125 °C	1 20 4	-	70	-				
Book receiver aurrent	I _{RRM}	T _J = 25 °C	I _F = 30 A dI _F /dt = 200 A/μs V _R = 200 V	-	3.5	-	A			
Peak recovery current		T _J = 125 °C		-	7.6	-				
Reverse recovery charge	Q _{rr}	T _J = 25 °C	VR - 200 V	-	50	-	nC			
		T _J = 125 °C		-	280	-	no			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C			
Thermal resistance, junction to case	R _{thJC}		-	0.95	1.4	°C/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	70				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-				
Weight			-	2.0	-	g			
weight			-	0.07	-	oz.			
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)			
Manting device		Case style D ² PAK (TO-263AB)	ETH3006SH						
Marking device		Case style TO-262AA ETH3							



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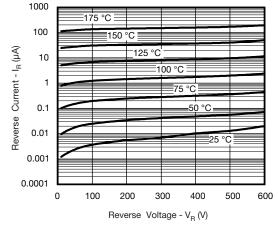


Fig. 1 - Typical Forward Voltage Drop Characteristics



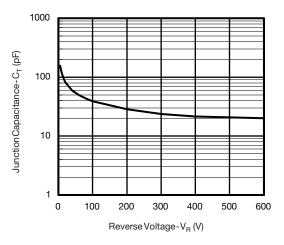
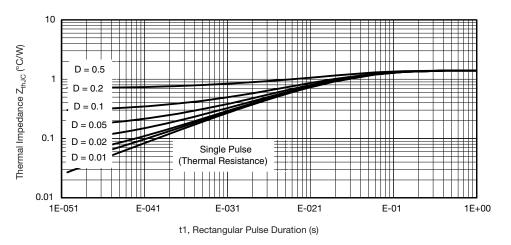
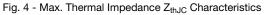


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





 Revision: 07-Jun-2023
 3
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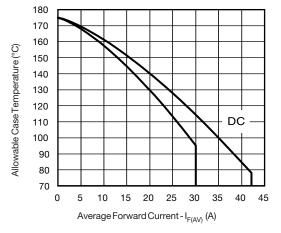


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

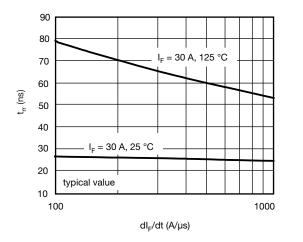


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

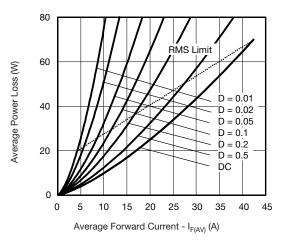


Fig. 6 - Forward Power Loss Characteristics

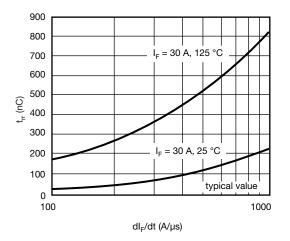


Fig. 8 - Typical Stored Charge vs. dl_F/dt



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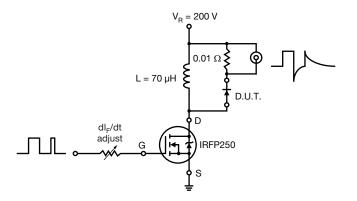


Fig. 9 - Reverse Recovery Parameter Test Circuit

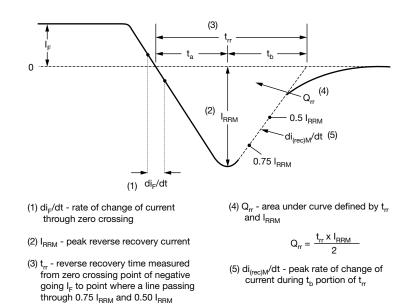
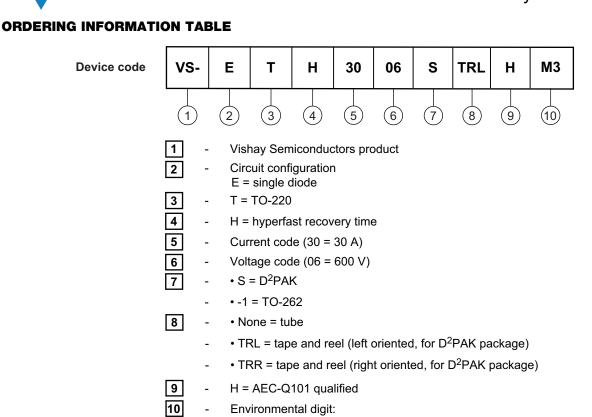


Fig. 10 - Reverse Recovery Waveform and Definitions

extrapolated to zero current.



-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION						
VS-ETH3006SHM3	50	Antistatic plastic tube						
VS-ETH3006-1HM3	50	Antistatic plastic tube						
VS-ETH3006STRRHM3	800	13" diameter reel						
VS-ETH3006STRLHM3	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS								
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?95046						
Dimensions	TO-262AA	www.vishay.com/doc?95419						
Part marking information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444						
	TO-262AA	www.vishay.com/doc?95443						
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?95032						

VS-ETH3006SHM3, VS-ETH3006-1HM3

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Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches

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SHA



SYMBOL	MILLIMETERS		INC	INCHES		NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 08-Jul-15

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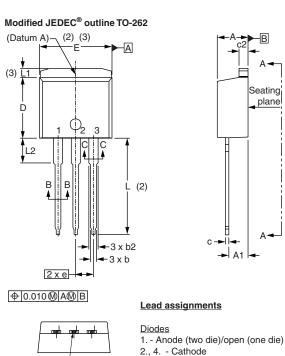
Outline Dimensions



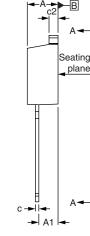
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TO-262

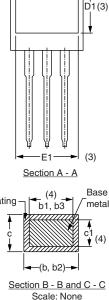
DIMENSIONS in millimeters and inches



Lead tip -



E1 Plating



Е

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. А 4.06 4.83 0.160 0.190 2.03 A1 3.02 0.080 0.119 b 0.51 0.99 0.020 0.039 b1 0.51 0.89 0.020 0.035 4 b2 1.14 1.78 0.045 0.070 1.14 1.73 0.045 0.068 4 b3 0.38 0.74 0.015 0.029 С 0.38 0.58 0.015 0.023 4 c1 1.14 1.65 0.045 0.065 c2 D 8.51 9.65 0.335 0.380 2 D1 6.86 8.00 0.270 0.315 3 Е 9.65 10.67 0.380 0.420 2, 3 E1 7.90 8.80 0.311 0.346 3 0.100 BSC 2.54 BSC е L 13.46 14.10 0.530 0.555 L1 _ 1.65 0.065 3 _ 3.36 0.132 0.146 L2 3.71

3. - Anode

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC TO-262 except A1 (maximum), (6) b (minimum), D1 (minimum) and L2 where dimensions derived the actual package outline

Revision: 11-Jul-2019

Document Number: 95419

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